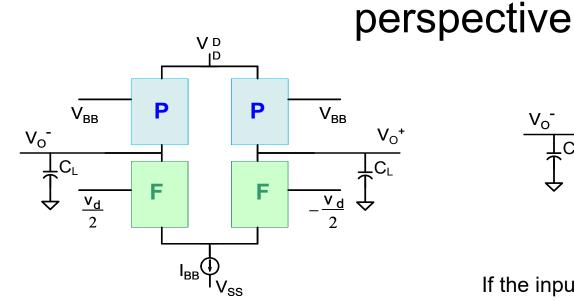
### EE 435

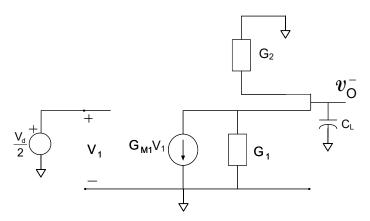
#### Lecture 6:

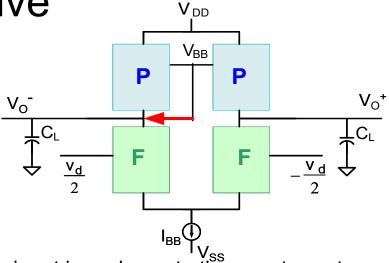
- Signal Swing
- Measurement/Simulation of High Gain Circuits
- Offset Voltage
- High Gain Single-Stage Op Amps

## Operation of Op Amp – A different



#### Small signal differential half-circuit





If the input impedance to the counterpart circuit is infinite and the quiescent values of the left and right drain voltages are the same, connecting the bias port of the quarter circuit to  $V_0^-$  instead of to  $V_{BB}$  will cause the signal current in the right counterpart circuit to be equal to that in the left counterpart circuit

This will double the signal current steered to V<sub>o</sub><sup>+</sup> and thus double the voltage gain!

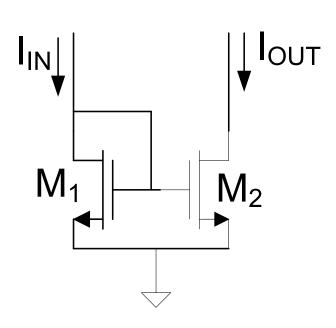
This will also eliminate the need for a 3 CMFB circuit!

# Review from last lecture: Amplifier Comparison

| Small Signal Parameter Domain                     |  |   |                                   |  |
|---|--|---|-----------------------------------|--|
| Reference Op Amp (single-ended ouput) (5T Op Amp) | $A_{vo} = \frac{1}{2} \frac{g_{m1}}{g_{o1} + g_{o3}}$  | $GB = \frac{g_{m1}}{2C_{L}}$  | $SR = \frac{g_{01}}{\lambda C_L}$ |  |
| Practical Parameter Domain                        |  |   |                                   |  |
| Reference Op Amp (single-ended ouput) (5T Op Amp) | $A_{v_0} = \left[\frac{1}{\lambda_{_1} + \lambda_{_3}}\right] \left(\frac{1}{V_{_{EB1}}}\right)$ | $GB = \left(\frac{P}{2V_{DD}C_{L}}\right) \bullet \left[\frac{1}{V_{EB1}}\right]$ | $SR = \frac{P}{2V_{DD}C_L}$       |  |

| Small Signal Parameter Domain                                   |  |  |                                    |  |
|---|--|--|------------------------------------|--|
| Op Amp with CM<br>Load and M <sub>1</sub> QC<br>(5T Op Amp wCM) | $A_{VO} = \frac{g_{m1}}{g_{O1} + g_{O3}}$  | $GB = \frac{g_{m1}}{C_L}$  | $SR = 2\frac{g_{01}}{\lambda C_L}$ |  |
| Practical Parameter Domain                                      |  |  |                                    |  |
| Op Amp with CM<br>Load and M <sub>1</sub> QC<br>(5T Op Amp wCM) | $A_{V0} = \left[\frac{2}{\lambda_1 + \lambda_3}\right] \left(\frac{1}{V_{EB1}}\right)$ | $GB = \left(\frac{P}{V_{DD}C_{L}}\right) \bullet \left[\frac{1}{V_{EB1}}\right]$ | $SR = \frac{P}{V_{DD}C_{L}}$       |  |

## **Basic Current Mirror**



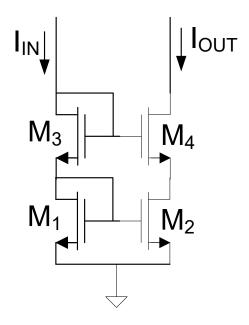
$$I_{IN} = \frac{\mu C_{OX} W_1}{2L_1} (V_{GS1} - V_T)^2$$

$$I_{OUT} = \frac{\mu C_{OX} W_2}{2L_2} \left(V_{GS2} - V_T\right)^2$$

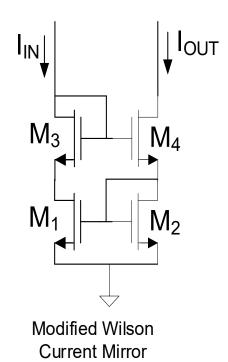
$$\frac{I_{OUT}}{I_{IN}} = \frac{W_2}{W_1} \frac{L_1}{L_2}$$

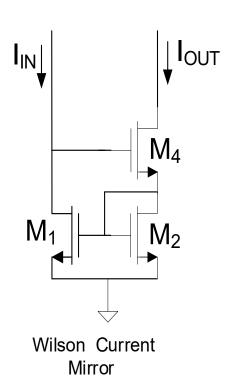
n-channel

### More Advanced Current Mirrors

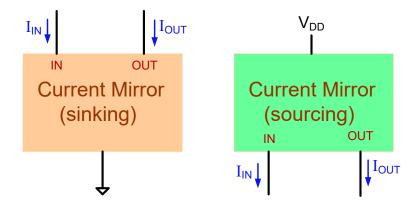


Cascode Current Mirror





## USPTO search on Feb 2, 2021



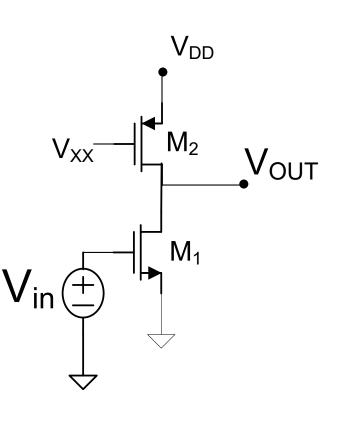
612 patents with "current and mirror" in title since 1976

26 patents with "current and mirror" in title from 2018 and 2020 searches

Number of patents/decade is about at the 3-decade average

Is there still an opportunity to contribute to the current mirror field?

Consider single-input amplifier first



To keep M₁ out of Triode Region

$$\mathcal{L}_1$$
:  $V_{OUT} > V_{iN} - V_{Tn}$ 

To keep M<sub>1</sub> out of Cutoff

$$\mathcal{L}_2$$
:  $V_{iN} > V_{Tn}$ 

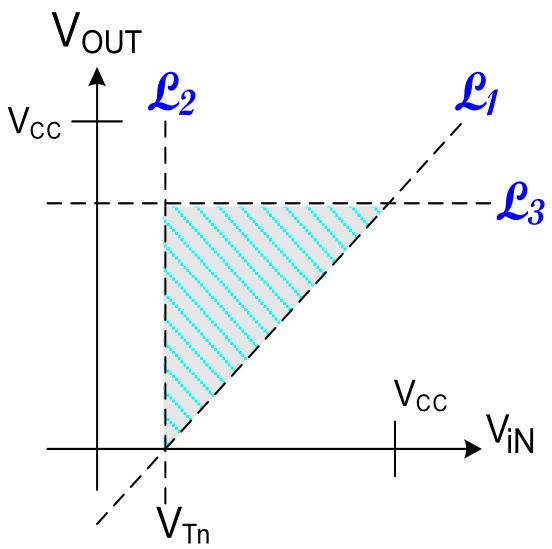
To keep M<sub>2</sub> out of Triode Region

$$\mathcal{L}_{3}: |V_{OUT} - V_{DD}| > |V_{XX} - V_{DD} - V_{Tp}|$$

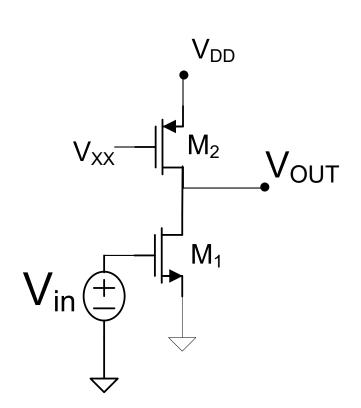
$$V_{XX} - V_{Tp} > V_{OUT}$$

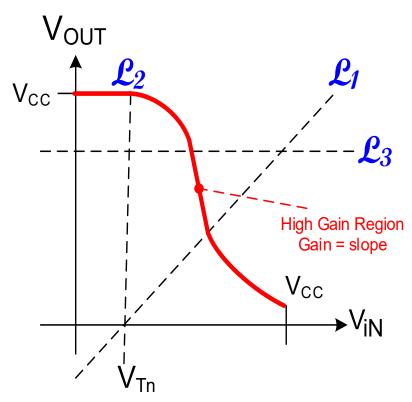
```
V_{OUT} > V_{iN} - V_{Tn}
\mathcal{L}_2: V_{iN} > V_{Tn}
\mathcal{L}_3: V_{XX} - V_{Tp} > V_{OUT}
  V_{\text{OUT}} \\
```

 $V_{CC}$ 



 $\mathcal{L}_{I}: V_{OUT} > V_{iN}-V_{Tn}$  $\mathcal{L}_2$ :  $V_{iN} > V_{Tn}$  $\mathcal{L}_3$ :  $V_{XX} - V_{Tp} > V_{OUT}$ 



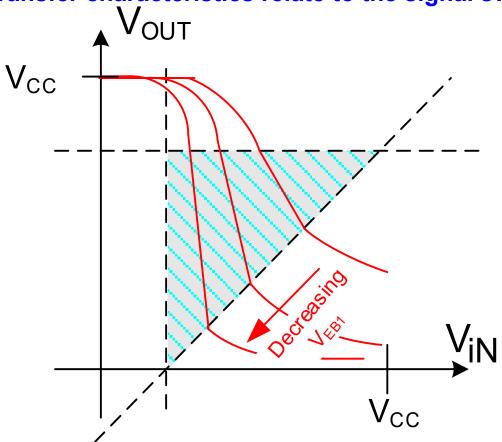


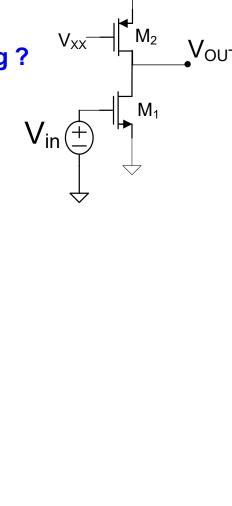
Transfer Characteristics of amplifier

#### How do the transfer characteristics relate to the signal swing?

Observe signal swing boundaries are same as operating region changes for transfer characteristics

How do the transfer characteristics relate to the signal swing?





 $V_{DD}$ 

For this circuit, high gain and large output signal swing for small  $V_{\text{EB1}}$ 

#### **Amplifier Comparison**

#### Small Signal Parameter Domain

Reference Op

Amp (single-ended ouput)

(5T Op Amp)

$$A_{vo} = \frac{1}{2} \frac{g_{m1}}{g_{o1} + g_{o3}}$$
  $GB = \frac{g_{m1}}{2C_{L}}$ 

$$GB = \frac{g_{m_1}}{2C_{m_1}}$$

$$SR = \frac{g_{01}}{\lambda C_1}$$

#### Practical Parameter Domain

Reference Op

Amp (single-ended ouput)

(5T Op Amp)

$$A_{v_0} = \left[\frac{1}{\lambda_{_1} + \lambda_{_3}}\right] \left(\frac{1}{V_{_{EB1}}}\right)$$

#### Small Signa

Op Amp with CM Load and M₁ QC (5T Op Amp wCM)

$$A_{VO} = \frac{g_{m1}}{g_{O1} + g_{O3}}$$

$$I_{D} = \frac{\mu C_{OX} W}{2L} \left( V_{GS} - V_{TH} \right)^{2} \left( 1 + \lambda V_{DS} \right)$$
$$g_{0} = \lambda I_{DQ}$$

λ not a BSIM Parameter

#### Practical Parameter Domain

Op Amp with CM Load and M₁ QC (5T Op Amp wCM)

$$A_{V0} = \left[\frac{2}{\lambda_1 + \lambda_3}\right] \left(\frac{1}{V_{EB1}}\right)$$

$$A_{V0} = \left[\frac{2}{\lambda_1 + \lambda_3}\right] \left(\frac{1}{V_{EB1}}\right) \quad GB = \left(\frac{P}{V_{DD}C_L}\right) \bullet \left[\frac{1}{V_{EB1}}\right]$$

$$SR = \frac{P}{V_{DD}C_{L}}$$

## **Output Impedance Calculation**

- g<sub>o</sub> is a critical parameter that appears in the smallsignal models of high-gain circuits
- With a square-law Spice Level 2 or Level 3 model of the transistor,

$$I_{D} = \frac{\mu C_{OX} W}{2L} (V_{GS} - V_{TH})^{2} (1 + \lambda V_{DS})$$

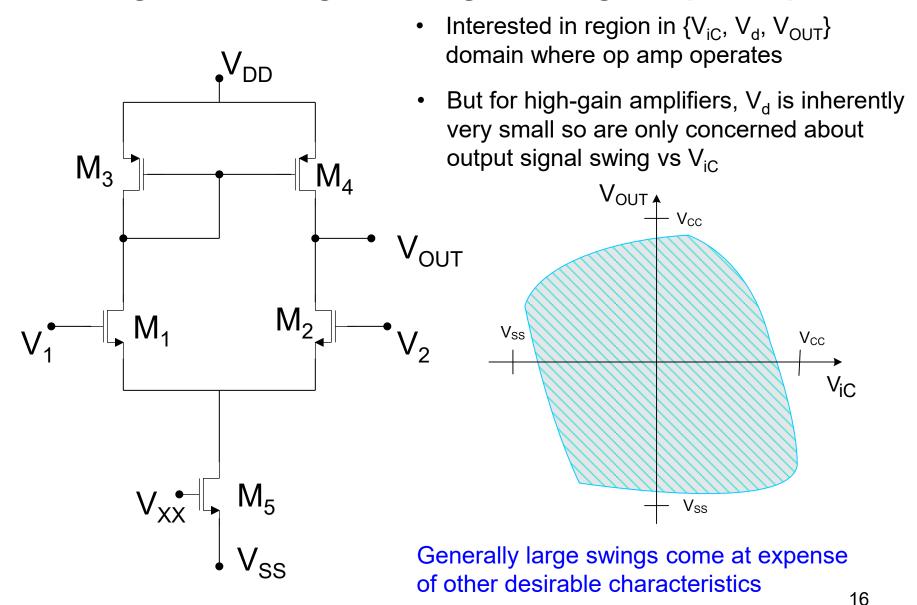
$$g_{0} = \frac{\partial I_{D}}{\partial V_{DS}} \bigg|_{Q-PT} = \left( \frac{\mu C_{OX} W}{2L} (V_{GS} - V_{TH})^{2} \lambda \right) \bigg|_{Q-PT} \simeq \lambda I_{DQ}$$

- But  $\lambda$  is not a parameter in a BSIM model and  $\lambda$  is often not even given in measured data such as that from MOSIS
- And  $g_0 = \frac{\partial I_D}{\partial V_{DS}}\Big|_{CPT}$  depends somewhat on L

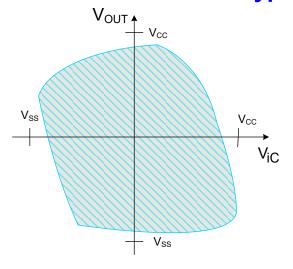
## Output Impedance Calculation

#### How to obtain g<sub>0</sub>

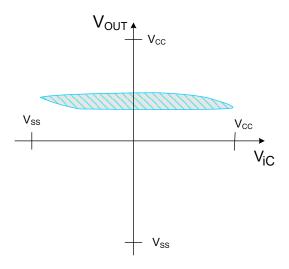
- Simulate single-transistor circuit with dimensions and operating point close to that of device used and obtain  $g_0 = \frac{\partial I_D}{\partial V_{DS}}\Big|_{C-PT}$
- If desired, define small-signal gain)  $\lambda \simeq \frac{\left.\frac{\partial I_D}{\partial V_{DS}}\right|_{Q-PT}}{I_{DQ}} \quad \text{(though actually $g_0$ is what is needed to obtain small-signal gain)}$
- Make a table of  $g_0$  (or  $\lambda$ ) for different L values in a given process
- g<sub>0</sub> is, however, still a model parameter



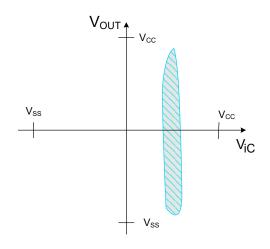
What type of signal swing is needed?



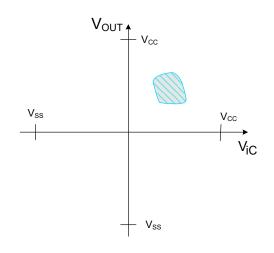
Wide  $V_{iC}$  and  $V_{OUT}$  range



Narrow V<sub>OUT</sub> and wide V<sub>iC</sub> range

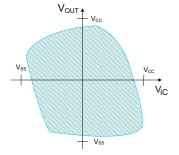


Narrow V<sub>iC</sub> and wide V<sub>OUT</sub> range



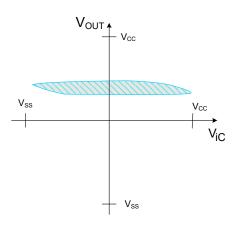
Narrow V<sub>iC</sub> and V<sub>OUT</sub> range <sup>1</sup>

What type of signal swing is needed?



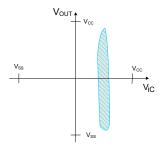
Wide V<sub>iC</sub> and V<sub>OUT</sub> range

Expected for catalog parts and overall I/O in many applications



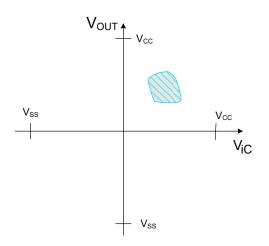
Narrow V<sub>OUT</sub> and wide V<sub>iC</sub> range

Acceptable when followed by high-gain stage



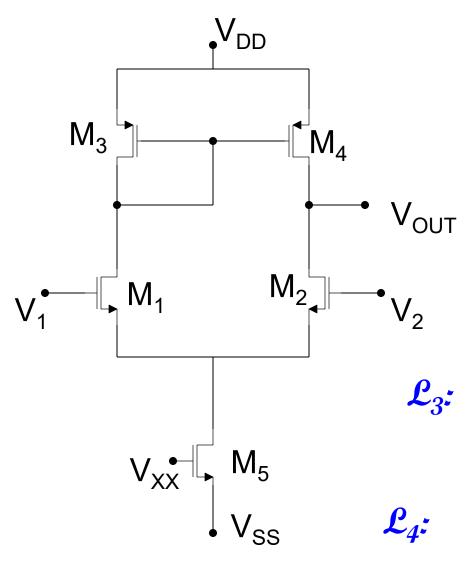
Narrow V<sub>iC</sub> and wide V<sub>OUT</sub> range

Acceptable when ViC is fixed



Narrow V<sub>iC</sub> and V<sub>OUT</sub> range

Acceptable when V<sub>iC</sub> fixed and 18 followed by high-gain stage



#### **Constraining Equations:**

To keep M<sub>2</sub> in Saturation:

$$\mathcal{L}_{1}$$
:  $V_{OUT} > V_{ic} - V_{T2}$ 

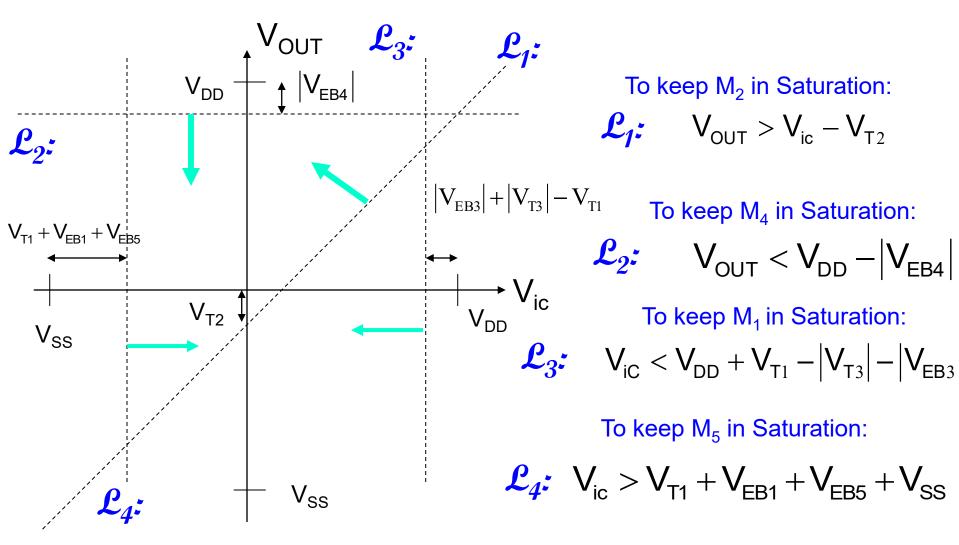
To keep 
$$M_4$$
 in Saturation:
$$V_{OUT} < V_{DD} - |V_{EB4}|$$
To keep  $M_4$  in Saturation:

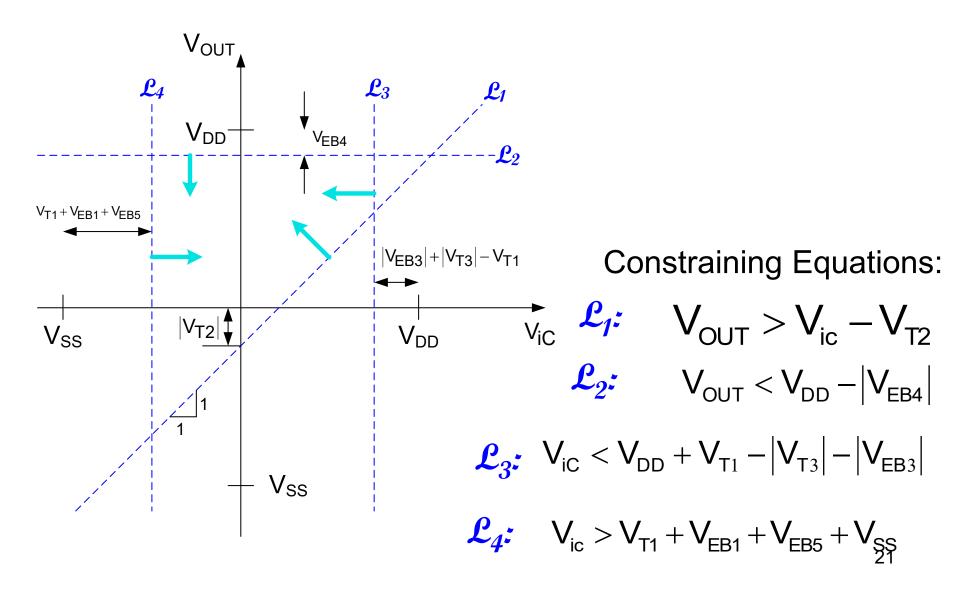
To keep M₁ in Saturation:

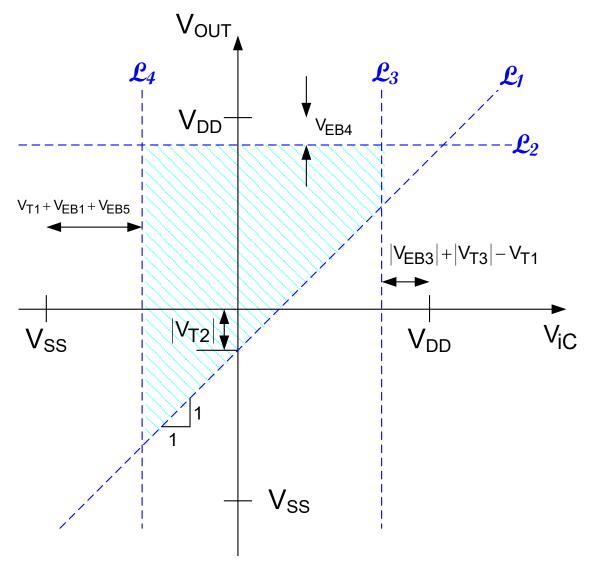
$$V_{iC} < V_{DD} + V_{T1} - |V_{T3}| - |V_{EB3}|$$

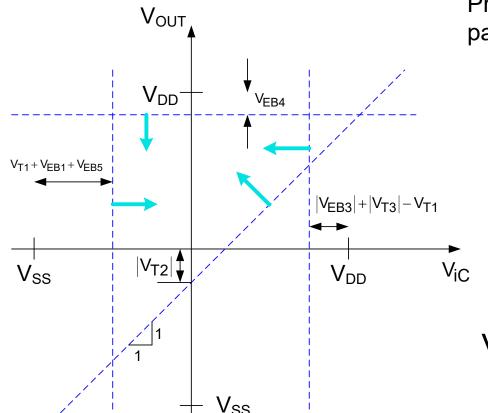
To keep M<sub>5</sub> in Saturation:

$$\mathcal{L}_{4}$$
:  $V_{ic} > V_{T1} + V_{EB1} + V_{EB5} + V_{SS}$ 









Preemptive comment: practical parameter domain for 5T Op Amp

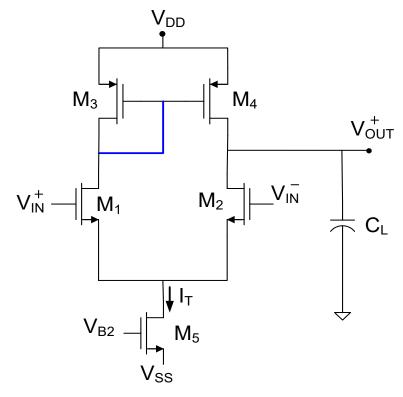
$$\{V_{EB1}V_{EB3}V_{EB5}P\}$$

#### **Constraining Equations:**

$$\begin{split} V_{OUT} > V_{ic} - V_{T2} \\ V_{OUT} < V_{DD} - \big| V_{EB4} \big| \\ V_{iC} < V_{DD} + V_{T1} - \big| V_{T3} \big| - \big| V_{EB3} \big| \\ V_{ic} > V_{T1} + V_{EB1} + V_{EB5} + V_{SS} \end{split}$$

- Signal swings are Important Performance Parameters !!
- Signal swing parameters are naturally in practical parameter domain
- Since V<sub>EB3</sub>=V<sub>EB4</sub>, small V<sub>EB3</sub> improves both output swing and V<sub>iC</sub> swing

### Design space for single-stage CM 5T op amp



How many independent design variables and how many constraints does this circuit have (assuming symmetry)?

Assume  $V_{SS}$ ,  $V_{DD}$ , and  $C_L$  fixed

Small-signal domain?

$$\{g_{m1}, g_{m3}, g_{m5}, g_{01}, g_{03}, g_{05}\}$$

(not independent)

Natural parameter domain?

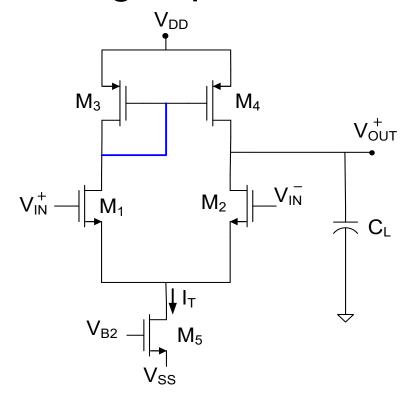
$$\{W_3/L_3, W_1/L_1, W_5/L_5, I_T\}$$

No constraints

A practical parameter domain?

No constraints

#### Design space for single-stage CM 5T op amp



Performance Parameters in Practical Parameter Domain  $\{V_{EB1} V_{EB3} V_{EB5} P\}$ :

$$A_{o} = \left[\frac{1}{\lambda_{_{1}} + \lambda_{_{3}}}\right] \left(\frac{2}{V_{_{EB1}}}\right)$$

$$GB = \left(\frac{P}{V_{DD}C_{L}}\right) \left[\frac{1}{V_{EB1}}\right]$$

$$SR = \frac{P}{(V_{DD} - V_{SS})C_{L}}$$

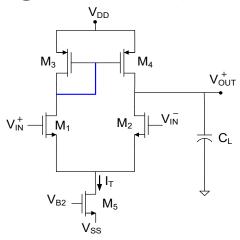
$$V_{OUT} < V_{DD} - \left|V_{EB3}\right|$$

$$V_{OUT} > V_{ic} - V_{T2}$$

$$V_{iC} < V_{DD} + V_{T1} - \left|V_{T3}\right| - \left|V_{EB3}\right|$$

$$V_{ic} > V_{T1} + V_{EB1} + V_{EB5} + V_{SS}$$

#### Design example for single-stage CM 5T op amp



Performance Parameters in Practical Parameter Domain { V<sub>EB1</sub> V<sub>EB3</sub> V<sub>EB5</sub> P}:

$$A_{\scriptscriptstyle 0} = \left[\frac{1}{\lambda_{\scriptscriptstyle 1} + \lambda_{\scriptscriptstyle 3}}\right] \left(\frac{2}{V_{\scriptscriptstyle EB1}}\right)$$

$$GB = \left(\frac{P}{V_{DD}C_{L}}\right)\left[\frac{1}{V_{EB1}}\right]$$

Assume design to meet  $A_0$ , GB and signal swing specs.

- 1. Select Parameter Domain (will use practical parameter domain)  $\{V_{\mathsf{FB}1}V_{\mathsf{FB}3}V_{\mathsf{FB}5}P\}$
- 2. Pick  $V_{EB1}$  to meet gain requirement ) {  $V_{EB3}$   $V_{EB5}$  P}

$$V_{EB1} = \left[ \frac{1}{\lambda_1 + \lambda_3} \right] \left( \frac{2}{A_0} \right)$$

- 3. Pick P to meet GB requirement { V<sub>ER1</sub> V<sub>EB3</sub> V<sub>EB5</sub>
- 4. Pick  $V_{EB3}$  and  $V_{EB5}$  to meet signal swing requirements
- Map back from the Practical Parameter Domain to the Natural Parameter domain (next page)

$$SR = \frac{P}{(V_{DD} - V_{SS})C_L}$$

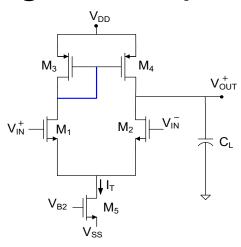
$$V_{\text{OUT}} < V_{\text{DD}} - \left| V_{\text{EB3}} \right|$$

$$V_{\text{OUT}} > V_{\text{ic}} - V_{\text{T2}}$$

$$V_{iC} < V_{DD} + V_{T1} - |V_{T3}| - |V_{EB3}|$$

$$V_{\text{ic}} > V_{\text{T1}} + V_{\text{EB1}} + V_{\text{EB5}} + V_{\text{SS}}$$

### Design example for single-stage CM 5T op amp



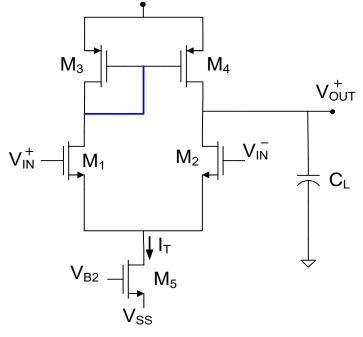
Performance Parameters in Practical Parameter Domain  $\{V_{EB1} V_{EB3} V_{EB5} P\}$ :

Mapping from Practical Parameter Domain {  $V_{EB1}$   $V_{EB3}$   $V_{EB5}$  P} to Natural Parameter Domain {  $W_1/L_1$   $W_3/L_3$   $W_5/L_5$   $I_T$ }

From expression 
$$I_{Dk} = \frac{\mu_k C_{ox} W_k}{2L_k} V_{EBk}^2$$
 it follows that

$$\begin{split} &\frac{W_{1}}{L_{1}} = \frac{1}{\mu_{n}C_{OX}V_{EB1}^{2}} \frac{P}{V_{DD} - V_{SS}} \\ &\frac{W_{3}}{L_{3}} = \frac{1}{\mu_{p}C_{OX}V_{EB3}^{2}} \frac{P}{V_{DD} - V_{SS}} \\ &\frac{W_{5}}{L_{5}} = \frac{2}{\mu_{n}C_{OX}V_{EB5}^{2}} \frac{P}{V_{DD} - V_{SS}} \\ &I_{T} = \frac{P}{V_{DD} - V_{SS}} \quad \text{or} \quad V_{B2} = V_{EB5} + V_{ss} + V_{THn} \end{split}$$

### Design space for single-stage CM 5T op amp



Performance Parameters in Natural Parameter Domain {  $W_1/L_1$   $W_3/L_3$   $W_5/L_5$   $I_T$ }:

$$\begin{aligned} A_{V0} = & \left[ \frac{\sqrt{4\mu_n \ C_{OX}}}{\lambda_1 + \lambda_3} \right] \left( \frac{\sqrt{\frac{W_1}{L_1}}}{\sqrt{I_T}} \right) \\ SR = & \frac{I_T}{C_L} \end{aligned}$$

$$GB = \left\lceil \frac{\sqrt{\mu_n \, C_{OX}}}{C_L} \right\rceil \sqrt{\frac{W_1}{L_1}} \sqrt{I_T}$$

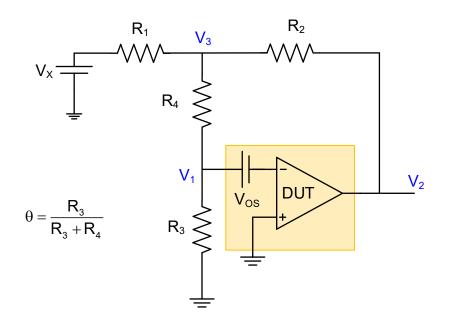
$$V_{OUT} < V_{DD} - \frac{\sqrt{I_T}}{\sqrt{\mu_p \, C_{OX}} \sqrt{\frac{W_3}{L_3}}}$$

$$V_{\text{OUT}} > V_{\text{ic}} - V_{\text{T2}}$$

 $V_{iC} < V_{DD} + V_{T1} - |V_{T3}| - \frac{\sqrt{I_T}}{\sqrt{\mu_p \, C_{OX}} \sqrt{\frac{W_3}{L_2}}}$  $V_{ic} > V_{T1} + \frac{\sqrt{I_T}}{\sqrt{\mu_n \, C_{OX}} \sqrt{\frac{W_1}{I_A}}} + \frac{\sqrt{I_T}}{\sqrt{\mu_n \, C_{OX}} \sqrt{\frac{W_5}{I_A}}} + V_{SS}$   $V_{OLIT} > V_{ic} - V_{T2}$ 

**Complicated Expressions (7) in Practical Parameter Domain**<sub>28</sub>

- Measurement of A<sub>V</sub> is challenging
  - Because it is so large
  - Even harder as A<sub>V0</sub> becomes larger
  - Offset voltage causes a problem
  - Embed in Feedback Network to Stabilize Operating Point
    - Stability must be managed (for 2 or more gain stages)
    - Use time varying input to distinguish signal information from offset
    - Must be well below first pole frequency to measure A<sub>v0</sub>
  - Measurement challenges often parallel simulation challenges
- Measurement of GB by indirect closed loop BW measurement is easy
- Measurement of R<sub>0</sub> is challenging
  - Often very small
  - Often challenging to avoid having measurement circuit cause output current to exceed I<sub>OMAX</sub>



Consider two inputs,  $V_{X1}$  and  $V_{X2}$ 

$$V_{21} = -A(\theta V_{31} - V_{OS})$$

$$V_{22} = -A(\theta V_{32} - V_{OS})$$

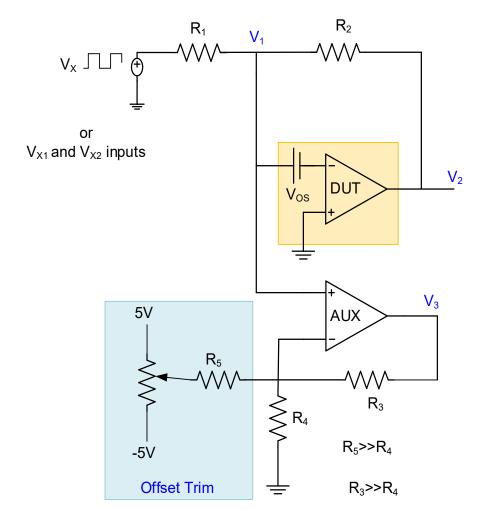
$$V_{31}(G_1 + G_2 + G_4) = G_1 V_{X1} + G_2 V_{21}$$

$$V_{32}(G_1 + G_2 + G_4) = G_1 V_{X2} + G_2 V_{22}$$

$$A = \frac{1}{\theta} \frac{V_{22} - V_{21}}{V_{31} - V_{32}}$$

$$V_{OS} = \theta \frac{V_{21}V_{32} - V_{31}V_{22}}{V_{21} - V_{22}}$$

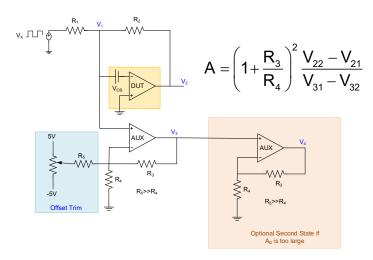
Not needed



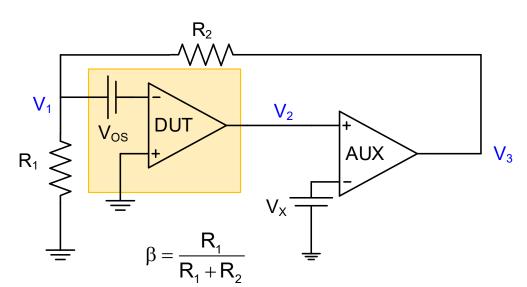
Consider two inputs,  $V_{X1}$  and  $V_{X2}$ 

$$A = \left(1 + \frac{R_3}{R_4}\right) \frac{V_{22} - V_{21}}{V_{31} - V_{32}}$$

Can also measure V<sub>OS</sub> with this circuit



Can add gain stage if A is very large

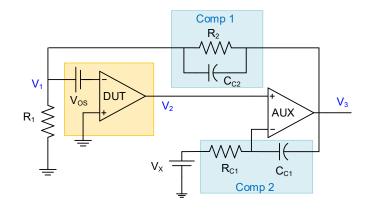


Consider two inputs,  $V_{X1}$  and  $V_{X2}$ 

$$V_{os} = \frac{\beta \left(V_{32} \frac{V_{x1}}{V_{x2}} - V_{31}\right)}{\left(\frac{V_{x1}}{V_{x2}} - 1\right)}$$

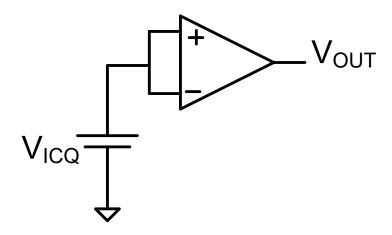
$$A_{v} = \frac{V_{x2} - V_{x1}}{\beta \left(V_{31} - V_{32}\right)}$$

- Must compensate this circuit and compensation may be a bit complicated
- Compensation beyond scope at this stage in EE 435



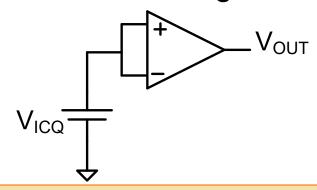
#### Offset Voltage

- Systematic Offset Voltage
- Random Offset Voltage

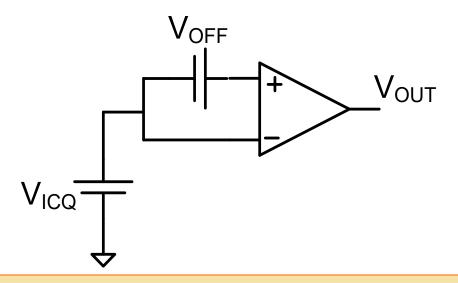


#### Offset Voltage

- Systematic Offset Voltage
- Random Offset Voltage



Definition: The output offset voltage is the difference between the desired output and the actual output when  $V_{id}$ =0 and  $V_{ic}$  is the quiescent common-mode input voltage.

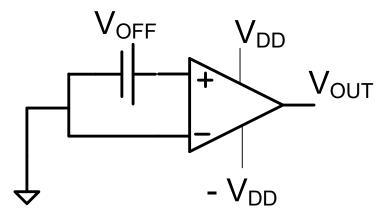


Definition: The input-referred offset voltage is the differential dc input voltage that must be applied to obtain the desired output when  $V_{ic}$  is the quiescent common-mode input voltage.

Note: V<sub>OFF</sub> is usually related to the output offset voltage by the expression

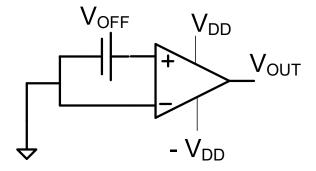
$$V_{OFF} = \frac{V_{OUTOFF}}{A_D}$$

Note:  $V_{OFF}$  is dependent upon  $V_{ICQ}$  although this dependence is usually quite weak and often not specified



When differential input op amps are biased with symmetric supply voltages, it is generally assumed that the desired quiescent input voltage Is 0V and the desired quiescent output voltage is 0V so  $V_{OFF}$  is the differential Input voltage needed to make  $V_{OUT}$ =0V.

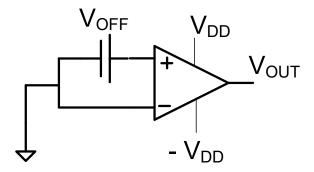
The input offset voltage is comprised of two parts, a systematic component and a random component



After fabrication there is no distinction made between  $V_{\text{OFFSYS}}$  and  $V_{\text{OSR}}$  and simply  $V_{\text{OFF}}$  is of concern

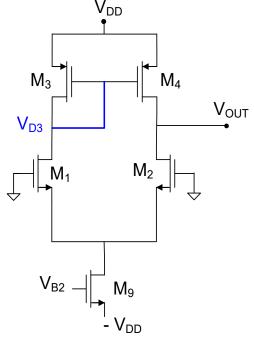
 $V_{OSR}$  is determined entirely by random variations in component values from their ideal value and will only be seen in a simulation if deviations are intentionally introduced (Monte Carlo Analysis if often used for predicting  $V_{OSR}$ )

It is expected that  $V_{OFFSYS}$  should be small (much smaller than  $V_{OSR}$ ) and it is the designer's responsibility to make this small



It is not necessary to make  $V_{OFFSYS}$  =0 although this can and is often done by making a minor tweak of matching critical parameters after the design of the op amp is almost complete

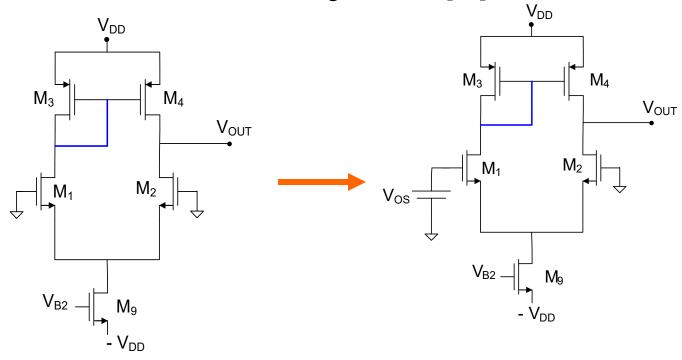
V<sub>OFFSYS</sub> can also be set to 0 by using a degree of freedom of the amplifier design variables but this is generally an unwise use of degrees of freedom (although some textbooks including Martin and Johns in Sec 5.1 do this!)



(If no missmatch is introduced, will be seeing only effects of systematic offset)

By symmetry, to force  $V_{OUT} = 0$ , it is necessary to have  $V_{D3} = 0$ 

- Making  $V_{D3}=0$  sets  $|V_{EB3}|=V_{DD}+V_{Tp}$  and results in the use of one degree of freedom!
- Making V<sub>EB3</sub> so large will severely limit the voltage swing at V<sub>OUT</sub>
- This shows why it is not wise to use a degree of freedom to make desired output voltage 0

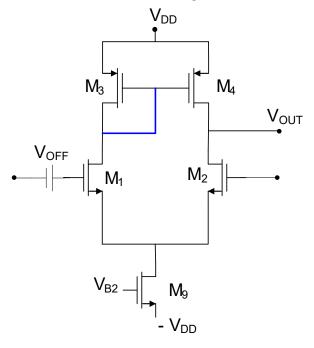


Can sweep a voltage in simulator at gate of M<sub>1</sub> to make V<sub>OUT</sub>=V<sub>OUT\_DESIRED</sub>

The value of  $V_{OS}$  that makes  $V_{OUT}=V_{OUT\ DES}$  is the systematic offset voltage

Can simply add the systematic offset voltage to input throughout rest of the design phase and then remove after design is complete or tweak at end of design to eliminate systematic offset.

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Usually  $V_{\text{OFF}}$  will change if changes in any design variables are made so re-simulation will be needed to get the correct value of  $V_{\text{OFF}}$ 

If  $V_{\text{OFF}}$  is not included, ac simulation of open-loop amplifier will usually not give desired results because small-signal models will be developed in simulator at incorrect operating point (often even in incorrect region of operation)

Alternative is to do ac simulations by embedding op amp into a FB configuration that will inherently compensate for offset voltage but issue of compensation must be addressed for amplifiers with two or more poles



Stay Safe and Stay Healthy!

## End of Lecture 6